IN THE CLAIMS

Please amend the following claims.

1-29 (cancelled)

30. (currently amended) A method of forming a semiconductor device comprising:

forming a gate electrode ~~having a first thickness~~ on a gate dielectric layer formed on a substrate;

forming a pair of source/drain regions on opposite sides of the gate electrode;

forming a semiconductor material film ~~having a second thickness~~ on the gate electrode and on the source/drain regions;

forming a pair of sidewall spacers on opposite sides of the gate electrode and the gate dielectric layer, the sidewall spacers having a spacer height;

depositing a metal layer over the sidewall spacers and the gate electrode to a thickness over the gate electrode sufficient to form a silicide having a height less than the spacer height;

forming a silicide layer ~~having a third thickness~~ on the semiconductor material film, the third thickness ~~at least twice a sum of the first thickness and the second thickness~~ less than the spacer height to confine the silicide to prevent silicide encroachment.~~; and~~

~~forming a pair of sidewall spacers having a height above the third thickness of the silicide layer on the semiconductor material film on the gate electrode.~~

31. (cancelled)

32. (previously presented) The method of claim 30, wherein the sidewall spacers comprise silicon nitride.

33. (cancelled)

34. (cancelled)

35. (cancelled)

36. (previously presented) The method of claim 30 wherein the gate electrode comprises polysilicon.

37. (previously presented) The method of claim 30 wherein the sidewall spacers are less than 300Å in width.